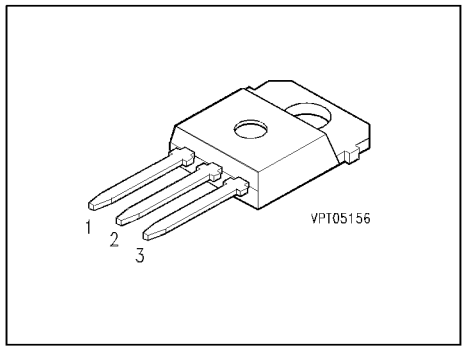
SIPMOS ® Power Transistor

- N channel
- Enhancement mode
- Avalanche-rated



Pin 1	Pin 2	Pin 3
G	D	S

Type	V_{DS}	I_D	$R_{DS(on)}$	Package	Ordering Code
BUZ 357	1000 V	5.1 A	2 Ω	TO-218 AA	C67078-S3110-A2

Maximum Ratings

Parameter	Symbol	Values	Unit
Continuous drain current T_C = 25 °C	I_D	5.1	A
Pulsed drain current T_C = 25 °C	I_{Dpuls}	20	
Avalanche current,limited by T_{jmax}	I_{AR}	5.1	
Avalanche energy,periodic limited by T_{jmax}	E_{AR}	18	mJ
Avalanche energy, single pulse I_D = 5.1 A, V_{DD} = 50 V, R_{GS} = 25 Ω L = 62 mH, T_j = 25 °C	E_{AS}	850	
Gate source voltage	V_{GS}	± 20	V
Power dissipation T_C = 25 °C	P_{tot}	125	W
Operating temperature	T_j	-55 ... + 150	°C
Storage temperature	T_{stg}	-55 ... + 150	
Thermal resistance, chip case	R_{thJC}	≤ 1	K/W
Thermal resistance, chip to ambient	R_{thJA}	75	
DIN humidity category, DIN 40 040		E	
IEC climatic category, DIN IEC 68-1		55 / 150 / 56	

Electrical Characteristics, at $T_j = 25°C$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Static Characteristics					
Drain- source breakdown voltage $V_{GS} = 0$ V, $I_D = 0.25$ mA, $T_j = 25$ °C	$V_{(BR)DSS}$	1000	-	-	V
Gate threshold voltage $V_{GS}=V_{DS}$, $I_D = 1$ mA	$V_{GS(th)}$	2.1	3	4	
Zero gate voltage drain current $V_{DS} = 1000$ V, $V_{GS} = 0$ V, $T_j = 25$ °C $V_{DS} = 800$ V, $V_{GS} = 0$ V, $T_j = 125$ °C	I_{DSS}	- -	- 10	1 100	µA
Gate-source leakage current $V_{GS} = 20$ V, $V_{DS} = 0$ V	I_{GSS}	-	10	100	nA
Drain-Source on-resistance $V_{GS} = 10$ V, $I_D = 3.2$ A	$R_{DS(on)}$	-	1.7	2	Ω

Electrical Characteristics, at $T_j = 25°C$, unless otherwise specified

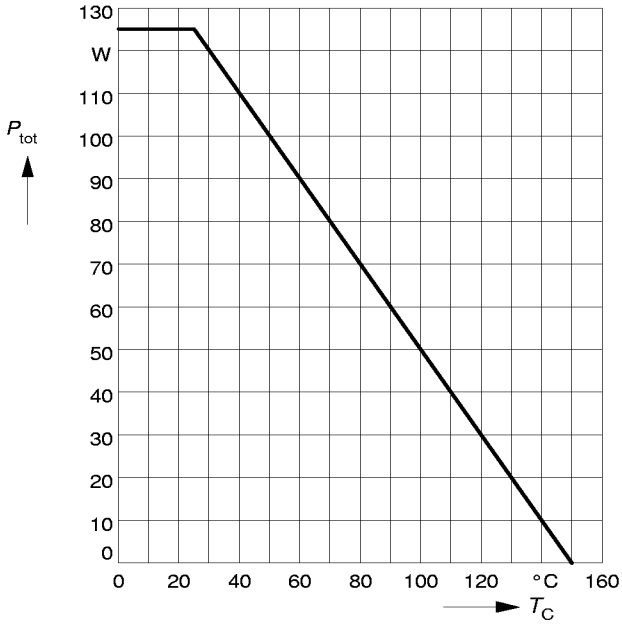
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Dynamic Characteristics					
Transconductance $V_{DS} \geq 2 * I_D * R_{DS(on)max}$, I_D = 3.2 A	g_{fs}	2.5	5.2	-	S
Input capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{iss}	-	1700	2200	pF
Output capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{oss}	-	170	300	
Reverse transfer capacitance V_{GS} = 0 V, V_{DS} = 25 V, f = 1 MHz	C_{rss}	-	80	120	
Turn-on delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.5 A R_{GS} = 50 Ω	$t_{d(on)}$	-	30	45	ns
Rise time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.5 A R_{GS} = 50 Ω	t_r	-	100	160	
Turn-off delay time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.5 A R_{GS} = 50 Ω	$t_{d(off)}$	-	400	520	
Fall time V_{DD} = 30 V, V_{GS} = 10 V, I_D = 2.5 A R_{GS} = 50 Ω	t_f	-	130	170	

Electrical Characteristics, at $T_j = 25°C$, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Reverse Diode					
Inverse diode continuous forward current $T_C = 25$ °C	I_S	-	-	5.1	A
Inverse diode direct current,pulsed $T_C = 25$ °C	I_{SM}	-	-	20	
Inverse diode forward voltage $V_{GS} = 0$ V, $I_F = 10$ A	V_{SD}	-	1	1.2	V
Reverse recovery time $V_R = 100$ V, $I_F = I_S$, $di_F/dt = 100$ A/µs	t_{rr}	-	1.5	-	µs
Reverse recovery charge $V_R = 100$ V, $I_F = I_S$, $di_F/dt = 100$ A/µs	Q_{rr}	-	6.5	-	µC

Power dissipation

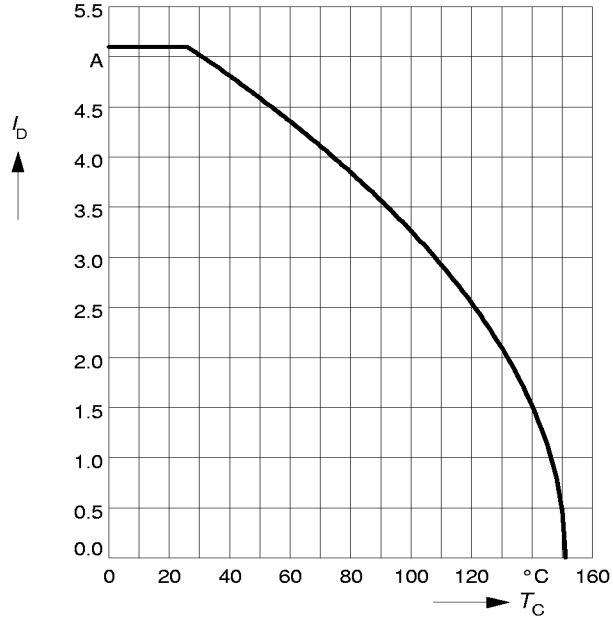
$P_{tot} = f(T_C)$



Drain current

$I_D = f(T_C)$

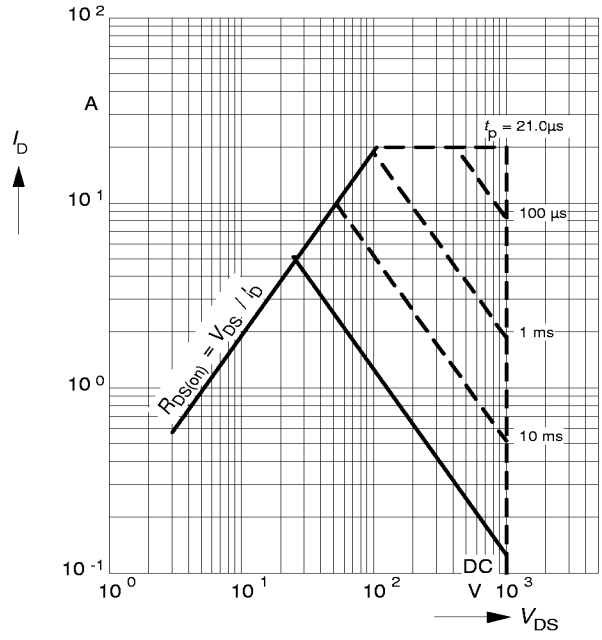
parameter: $V_{GS} \geq 10$ V



Safe operating area

$I_D = f(V_{DS})$

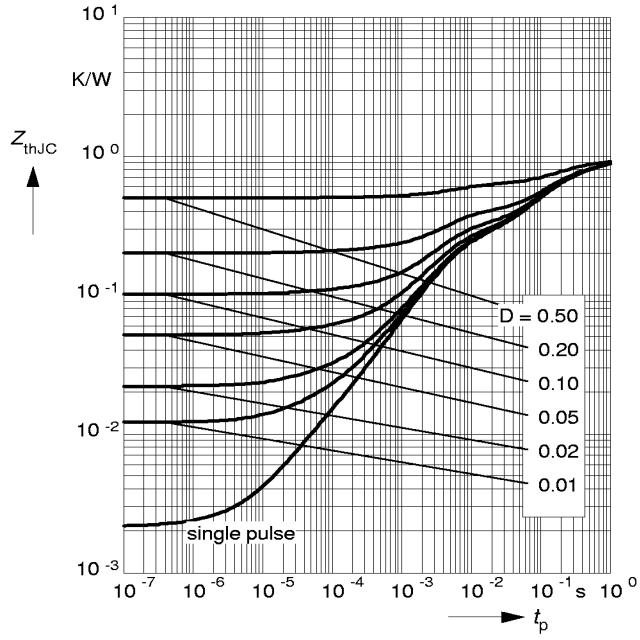
parameter: $D = 0.01$, $T_C = 25$°C



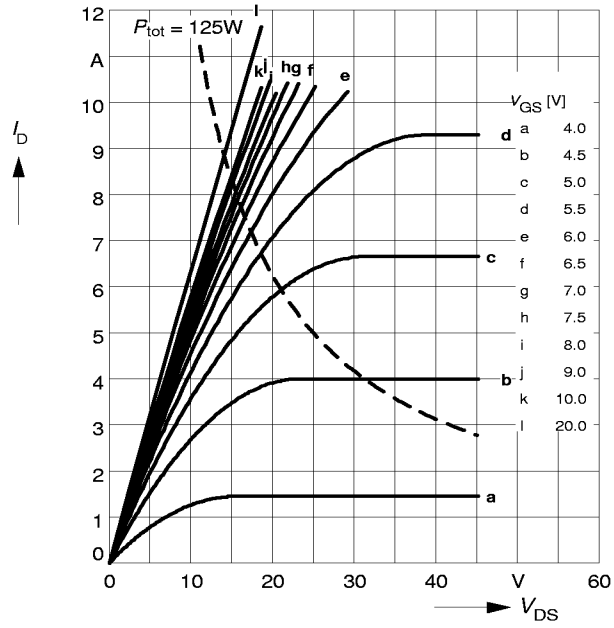
Transient thermal impedance

$Z_{th\,JC} = f(t_p)$

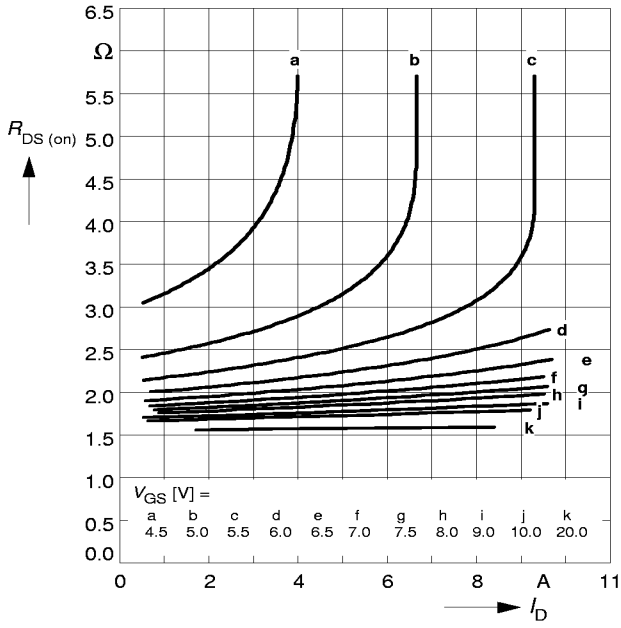
parameter: $D = t_p / T$



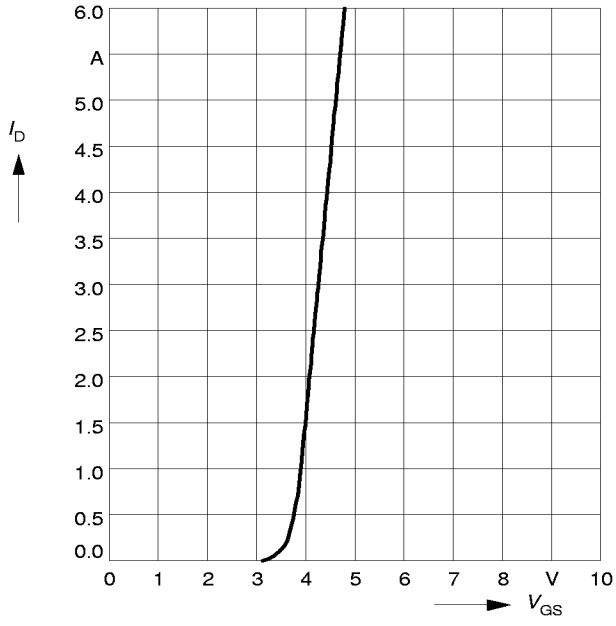
Typ. output characteristics
$I_D = f(V_{DS})$
parameter: t_p = 80 µs



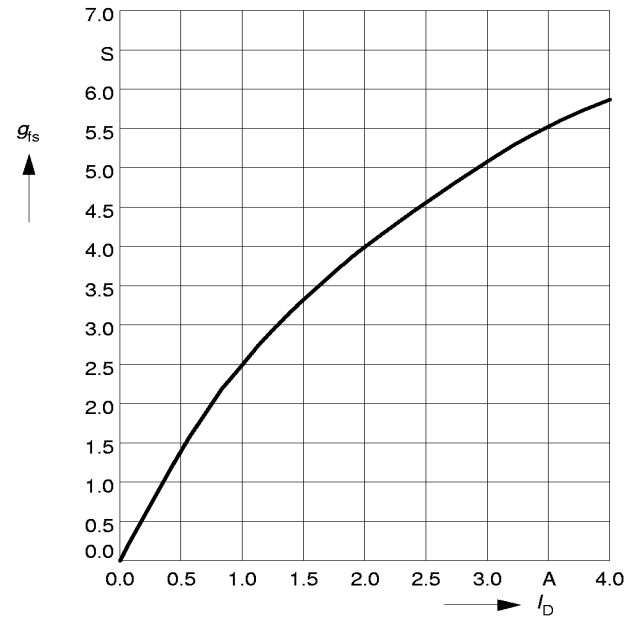
Typ. drain-source on-resistance
$R_{DS\,(on)} = f(I_D)$
parameter: t_p = 80 µs, T_j = 25 °C



Typ. transfer characteristics $I_D = f(V_{GS})$
parameter: t_p = 80 µs
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

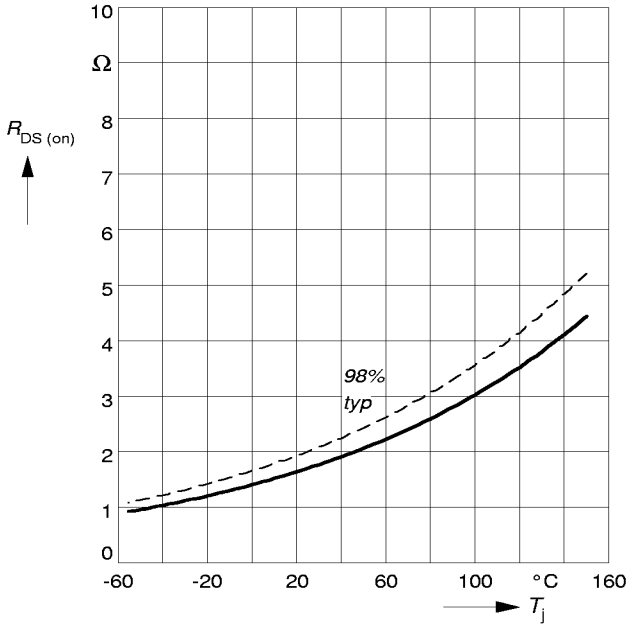


Typ. forward transconductance $g_{fs} = f(I_D)$
parameter: t_p = 80 µs,
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



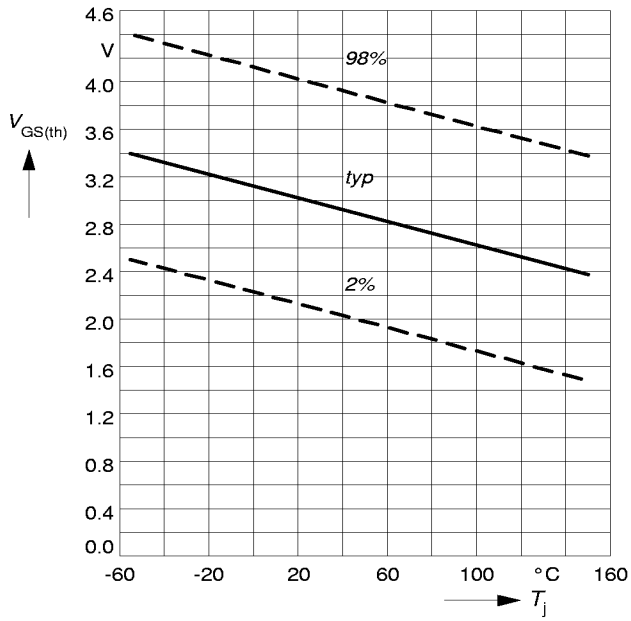
Drain-source on-resistance

$R_{DS\ (on)} = f(T_j)$
parameter: I_D = 3.2 A, V_{GS} = 10 V



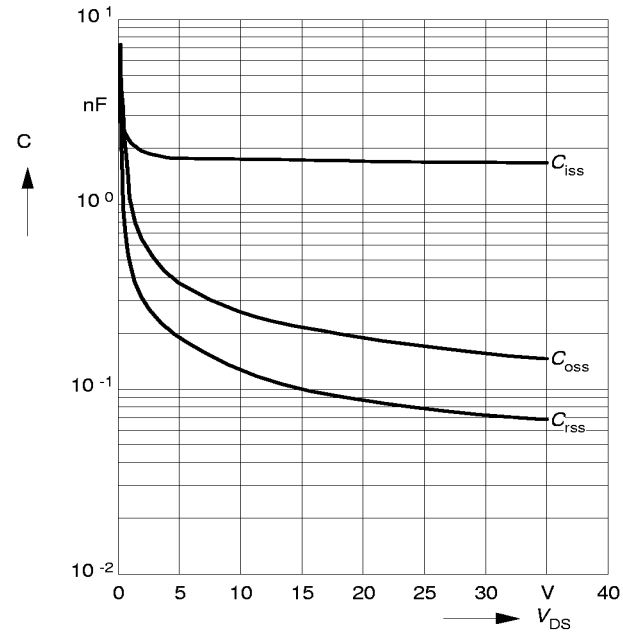
Gate threshold voltage

$V_{GS\ (th)} = f(T_j)$
parameter: $V_{GS} = V_{DS}$, I_D = 1 mA



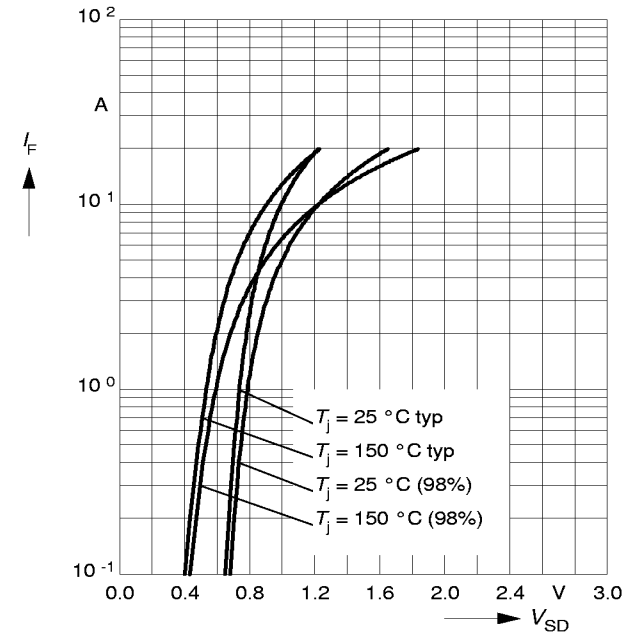
Typ. capacitances

$C = f(V_{DS})$
parameter: V_{GS} = 0V, f = 1MHz

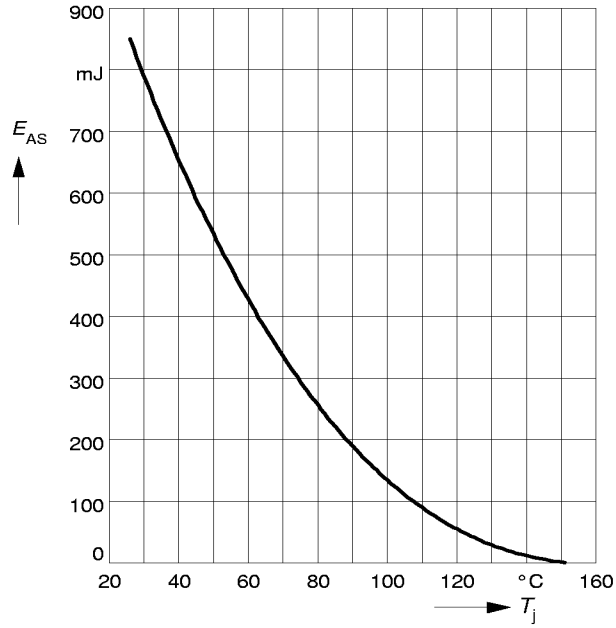


Forward characteristics of reverse diode

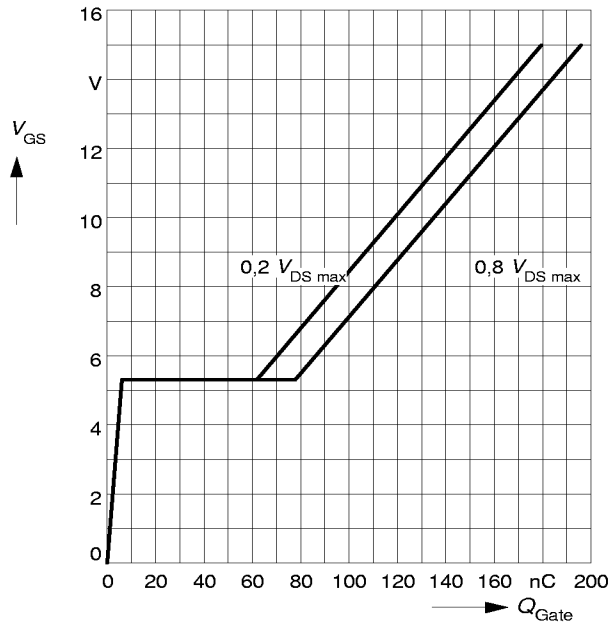
$I_F = f(V_{SD})$
parameter: T_j, t_p = 80 µs



Avalanche energy $E_{AS} = f(T_j)$
parameter: I_D = 5.1 A, V_{DD} = 50 V
R_{GS} = 25 Ω, L = 62 mH



Typ. gate charge
$V_{GS} = f(Q_{Gate})$
parameter: $I_{D\ puls}$ = 8 A



Drain-source breakdown voltage
$V_{(BR)DSS} = f(T_j)$